

RACOVĂȚ, O., EVTODIEV, I., ROTARU, I. et al. Optical properties of compounds with submicron points obtained through Ga_2S_3 intercalation with Cd. In: Fizică și tehnică: procese, modele, experimente. 2012, nr. 2, pp. 32-36

Luminescence and optical absorption spectra of Ga_2S_3 single crystals were investigated at temperatures of 78 K and 293 K. Optical band gap is equal to 3.27 eV and 3.457 eV at 293 K and 78 K respectively. Luminescence spectrum of single crystal lamellas at temperature of 78K consists of three bands with peaks at 2.04 eV, 1.84 eV and 1.66 eV. Native structural defects form deep recombination and electronic capture levels localized within the Ga_2S_3 band gap.